

# Temperature study of spin torque efficiencies in Ta/CoFeB/MgO with perpendicular magnetic anisotropy



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## MOTIVATION

Comprehensive approach to spin transfer torque via spin Hall effect in Ta/CoFeB requires precise characterization of Ta microstructure, examination of Ta/CoFeB interface and Ta layer influence on magnetic properties, which leads to extension of spin diffusion model:

Effective spin Hall angle  $\theta_{SH} \equiv \theta_{SH}^N(\theta_{SH}^N, \theta_{SH}^I, \theta_{AH}^F)$  — anomalous Hall angle of the ferromagnetic metal

spin Hall angle of nonmagnetic metal  $\theta_{SH}^N$  spin Hall angle of the interfacial layer  $\theta_{SH}^I$

## SAMPLES CHARACTERIZATION

$d_N$  Ta/0.9 Co<sub>40</sub>Fe<sub>40</sub>B<sub>20</sub>/5 MgO/1 Ta  $d_N = 5, 10, 15$  [nm]

Sputtering deposition method, 20 min post-annealing in 330°

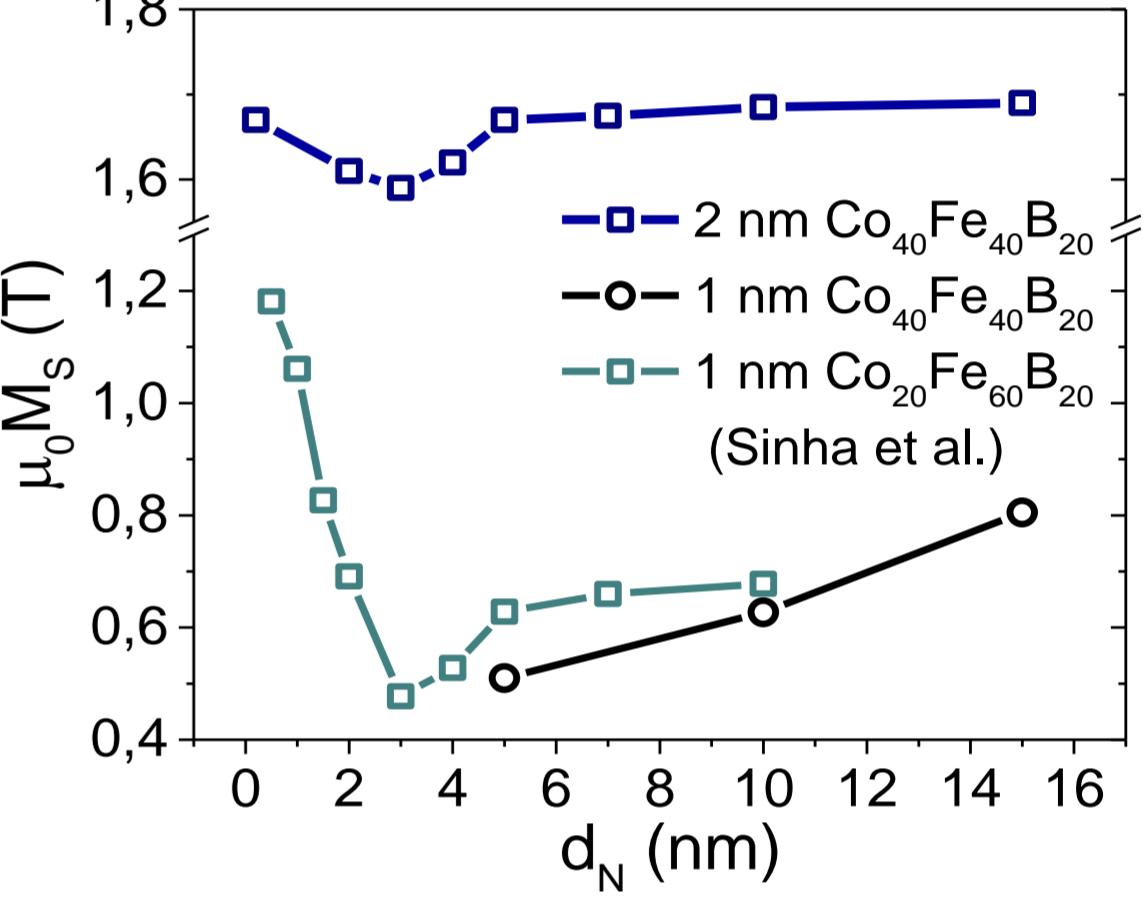
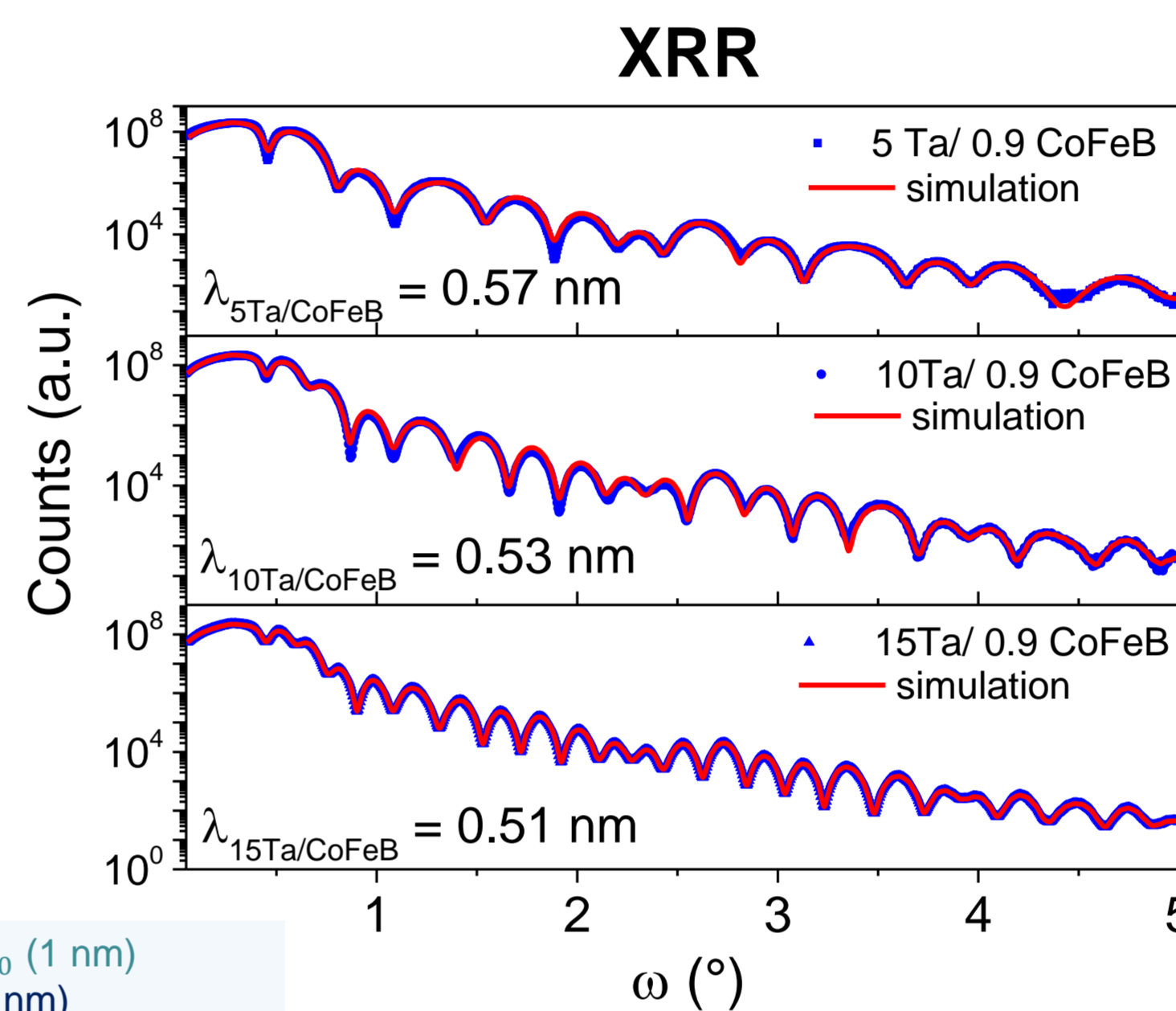
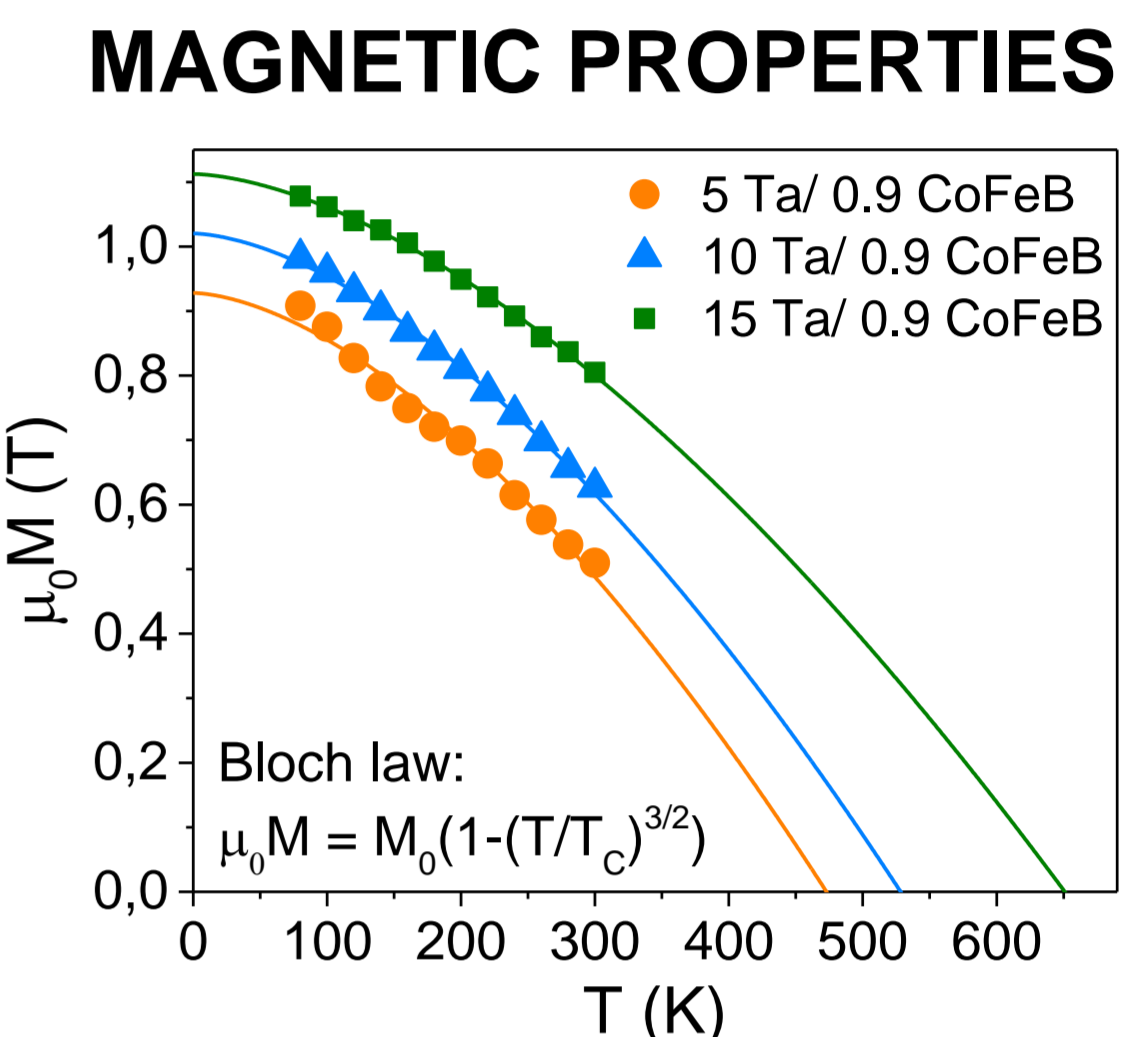
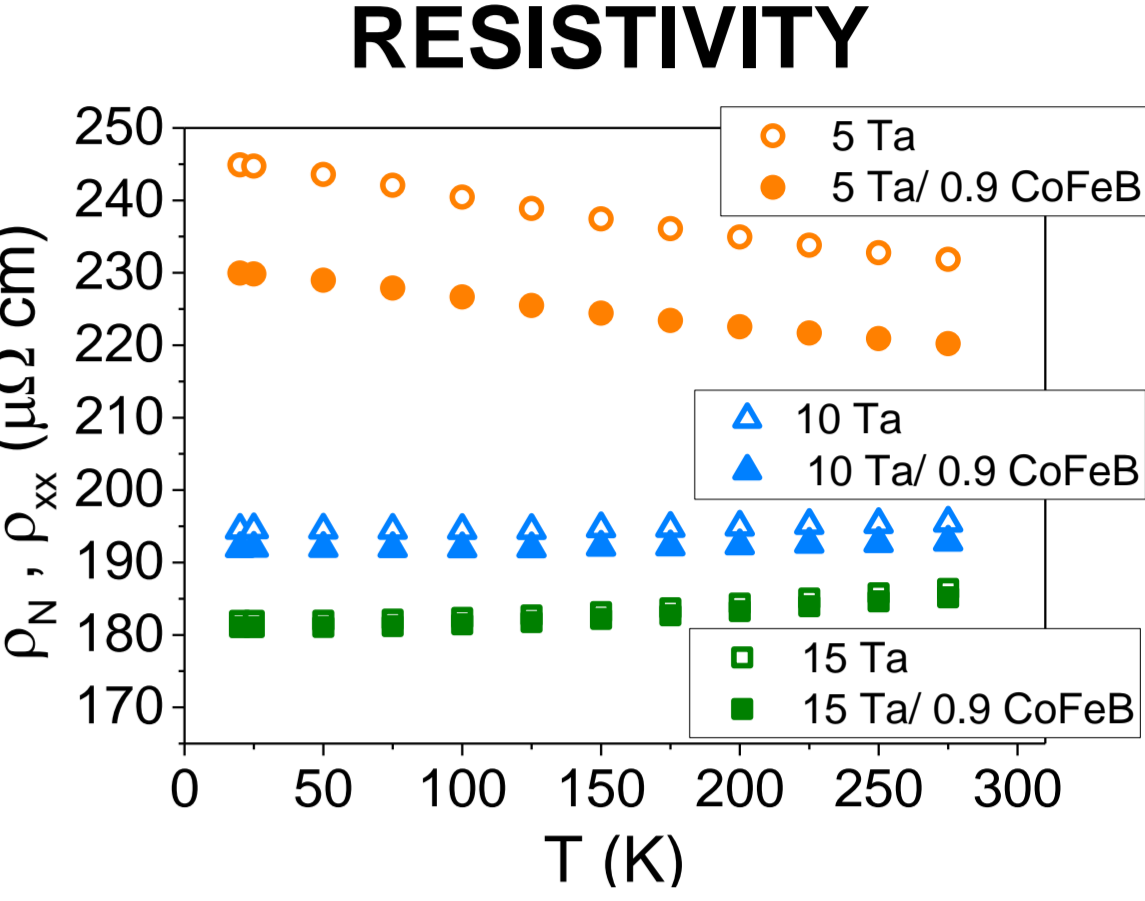
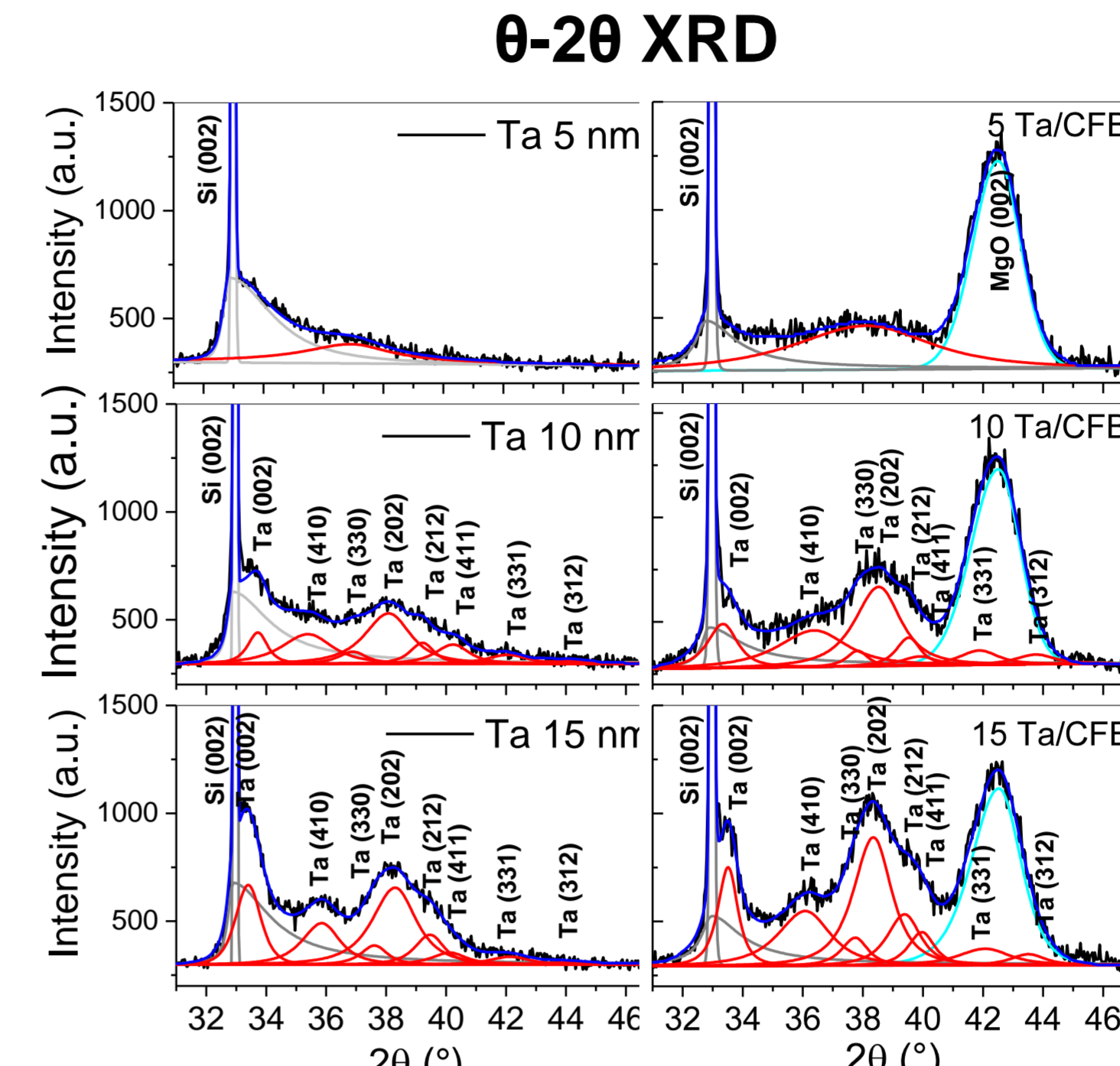
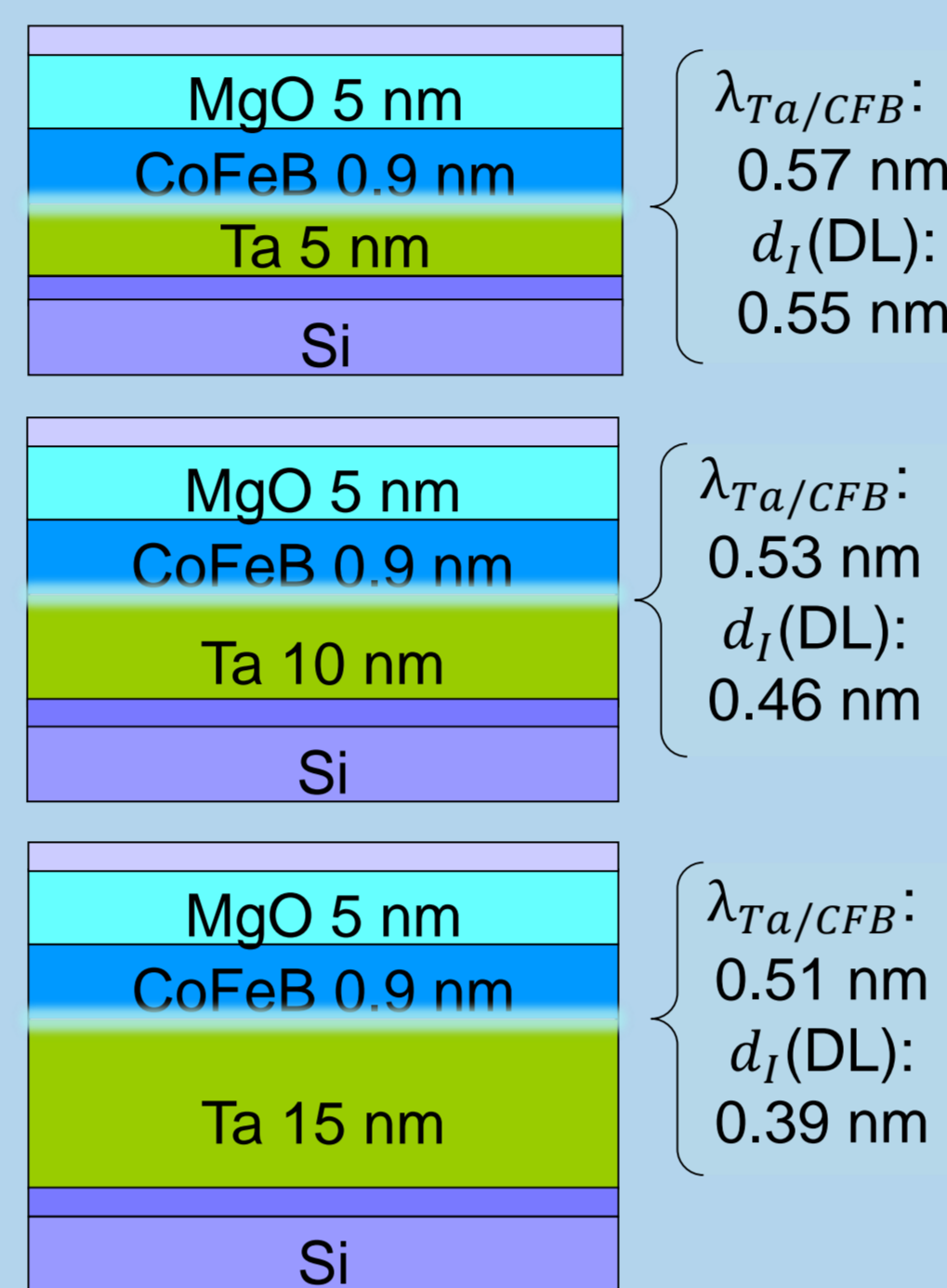
XRD: amorphous 5 nm Ta,  $\beta$ -phase in 10 nm and 15 nm of Ta

XRR: rough Ta/CoFeB interface  $\lambda_{Ta/CFB} \sim 0.57 - 0.51$  nm

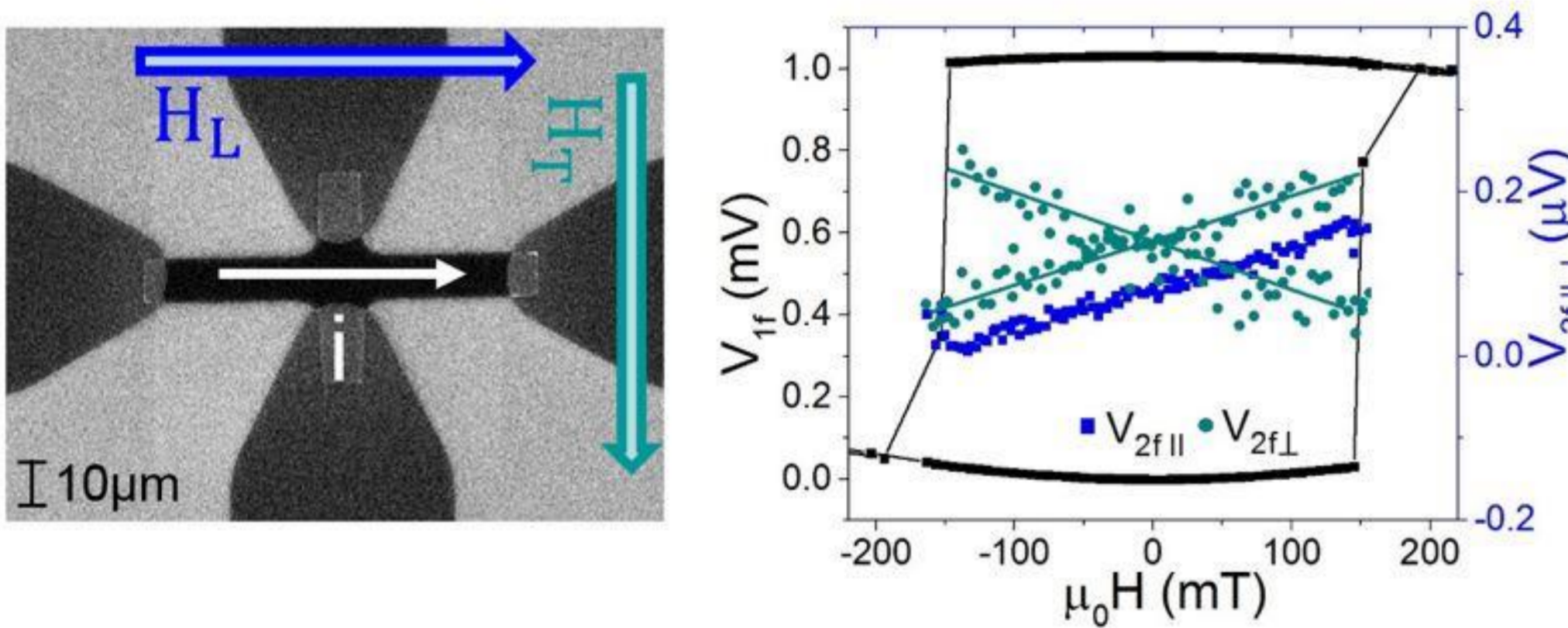
The highest resistivity for amorphous 5 nm Ta

Magnetic properties: Perpendicular magnetic anisotropy, Bloch low temperature dependence of spontaneous magnetization  $M$ , characteristic minimum of saturation magnetization  $M_S$  for  $d_N \approx 3$  nm

Significant magnetic dead layer (DL) thickness  $\approx 0.55-0.39$  nm



## HARMONIC HALL VOLTAGE MEASUREMENTS



J. Sinha et al. APL **102**, 242405 (2013) Ta(0-10 nm)/Co<sub>20</sub>Fe<sub>60</sub>B<sub>20</sub> (1 nm)  
 J. Kim et al. PRB **89**, 174424 (2014) Ta(1.3 nm)/Co<sub>20</sub>Fe<sub>60</sub>B<sub>20</sub> (1 nm)  
 X. Qiu et al. Scientific Reports **4**, 4491 (2014) Ta(2 nm)/Co<sub>40</sub>Fe<sub>40</sub>B<sub>20</sub> (0.8 nm)  
 C. Avci et al. PRB **89**, 214419 (2014) Ta(3 nm)/Co<sub>60</sub>Fe<sub>20</sub>B<sub>20</sub> (0.9 nm)  
 L. Liu et al. (after C. Avci) Ta(6 nm)/CoFeB(1 nm)  
 C. Zhang et al. Appl. Phys. Lett. **103**, 262407 (2013) Ta(2.5 nm)/CoFeB(1 nm)

## SPIN TORQUE EFFICIENCIES

Longitudinal ((anti)damping-like DL) and transverse (field-like FL) components of spin-orbit torque-induced effective field:

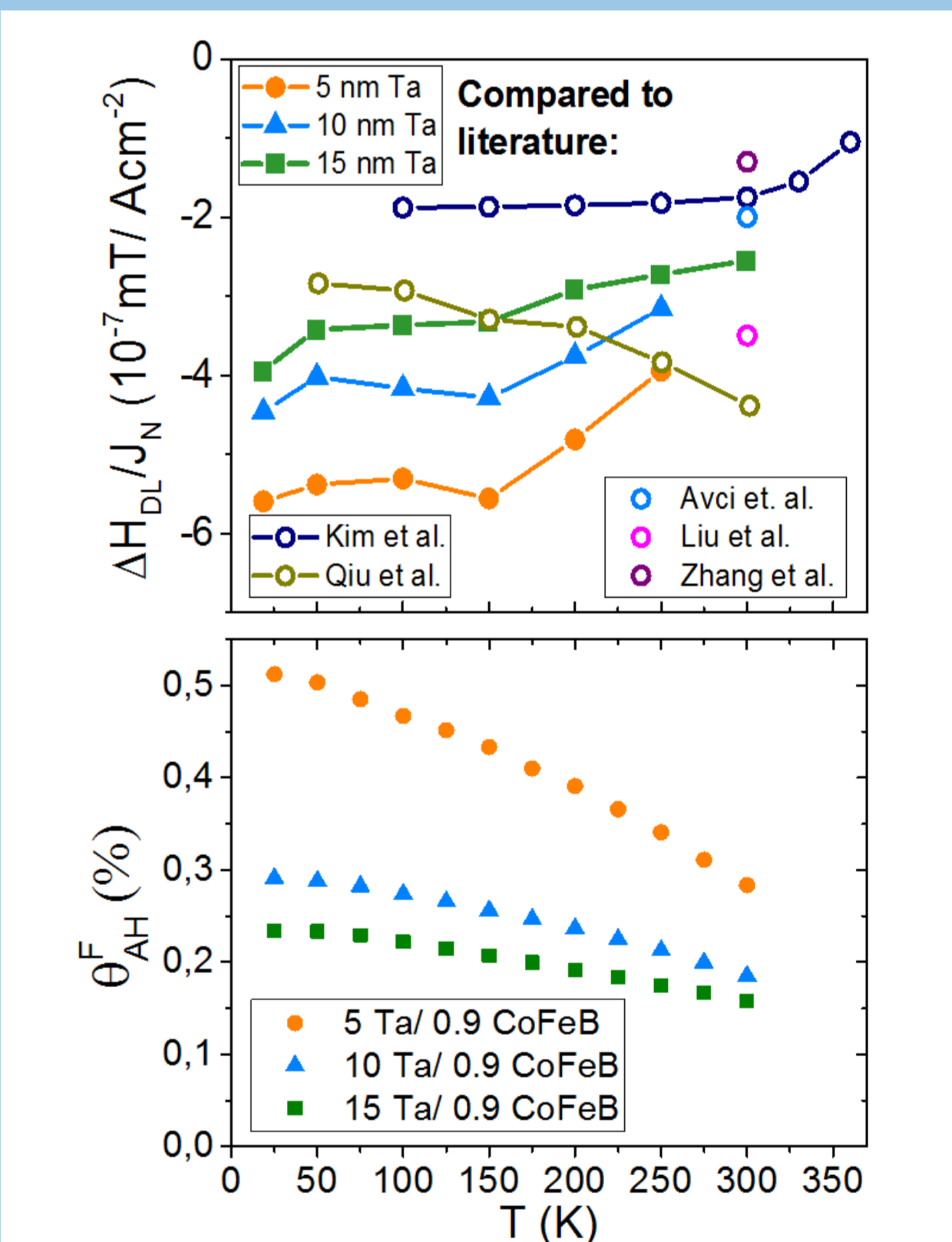
$$\Delta H_{DL, FL} = -2 \frac{\partial V_{2f} / \partial H_{DL, FL}}{\partial^2 V_{1f} / \partial H_{DL, FL}^2} \frac{\Delta R_{PHE}}{\Delta R_{AHE}} < 3\%$$

(Anti)damping-like and field-like torque efficiencies:

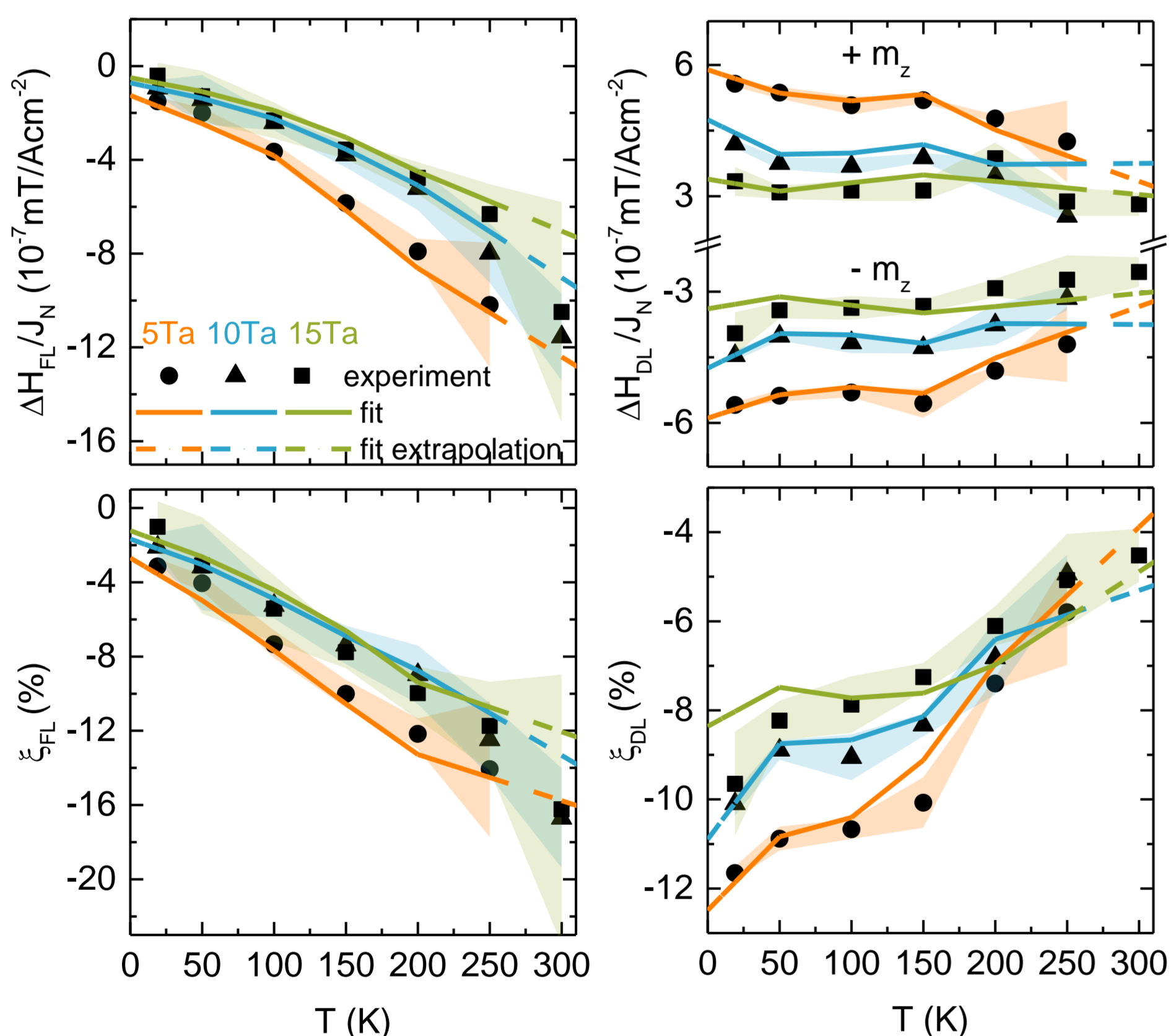
$$\xi_{DL, FL} = \frac{\Delta H_{DL, FL} \cdot 2e\mu_0 M_S d_F}{J_N \cdot \hbar}$$

## ANOMALOUS HALL EFFECT

Anomalous Hall angle as a ratio of AH resistivity and longitudinal resistivity:  $\theta_{AH}^F = \frac{\rho_{AHE}}{\rho_{xx}} < 0.5\%$



## RESULTS AND FITTING



## EXTENTION TO SPIN DIFFUSION MODEL

Assumptions:

- SML = 5%
- $\lambda_N = 1.5$  nm
- $\lambda_N, SML \sim \text{const}(T)$

Spin Memory Loss: interface thickness

$$SML = (1 - \exp(-\frac{d_I}{\lambda_I})) \cdot 100\%$$

Drift diffusion equations for spin currents in the nonmagnetic metal (N) and in the interface layer (I):

$$j_s^N(z) = -\frac{1}{2e\rho_N} \frac{\partial \mu_s^N(z)}{\partial z} - \theta_{SH}^N J_N \hat{y}$$

$$j_s^I(z) = -\frac{1}{2e\rho_I} \frac{\partial \mu_s^I(z)}{\partial z} - \theta_{SH}^I J_N \hat{y}$$

(Anti)damping-like component:

$$\Delta H_{DL} = \mp \frac{\hbar}{2e} \frac{J_N}{\mu_0 M_S d_F} \theta_{SH}^N \frac{\tanh(\frac{d_N}{2\lambda_N}) \text{csch}(\frac{d_I}{\lambda_I}) + \alpha [\tanh(\frac{d_I}{2\lambda_I}) \coth(\frac{d_N}{\lambda_N}) - \frac{\rho_I \lambda_I}{\rho_N \lambda_N}]}{\coth(\frac{d_N}{\lambda_N}) \coth(\frac{d_I}{\lambda_I}) + \frac{\rho_I \lambda_I}{\rho_N \lambda_N}} \frac{g_r (1 + g_r) + g_i^2}{(1 + g_r)^2 + g_i^2} + m_z, -m_z$$

Field-like component:

$$\Delta H_{FL} = -\frac{\hbar}{2e} \frac{J_N}{\mu_0 M_S d_F} \theta_{SH}^N \frac{\tanh(\frac{d_N}{2\lambda_N}) \text{csch}(\frac{d_I}{\lambda_I}) + \alpha [\tanh(\frac{d_I}{2\lambda_I}) \coth(\frac{d_N}{\lambda_N}) - \frac{\rho_I \lambda_I}{\rho_N \lambda_N}]}{\coth(\frac{d_N}{\lambda_N}) \coth(\frac{d_I}{\lambda_I}) + \frac{\rho_I \lambda_I}{\rho_N \lambda_N}} \frac{g_i}{(1 + g_r)^2 + g_i^2}$$

Real and imaginary parts of spin-mixing conductance  $G_r(T) \sim \text{const}$ ,  $G_i(T) \sim T$

$$g_{r,i} = 2G_{r,i} \frac{\coth(\frac{d_N}{2\lambda_N}) \coth(\frac{d_I}{\lambda_I}) + \frac{\rho_I \lambda_I}{\rho_N \lambda_N}}{\frac{1}{\rho_I \lambda_I} \coth(\frac{d_N}{\lambda_N}) + \frac{1}{\rho_N \lambda_N} \coth(\frac{d_I}{\lambda_I})}$$

## CONCLUSION

Extended spin diffusion model allows to obtain the temperature dependences of  $\theta_{SH}^N$  and  $\theta_{SH}^I$  components.

